



# SIGC20T120

## IGBT<sup>3</sup> Chip

### FEATURES:

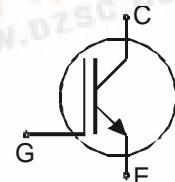
- 1200V Trench + Field Stop technology
- low turn-off losses
- short tail current
- positive temperature coefficient
- easy paralleling

### This chip is used for:

- power module

### Applications:

- drives



Chip Type	V <sub>CE</sub>	I <sub>Ch</sub>	Die Size	Package	Ordering Code
SIGC20T120	1200V	15A	4.41 x 4.47 mm <sup>2</sup>	sawn on foil	Q67050-A4103-A001

### MECHANICAL PARAMETER:

Raster size	4.41 x 4.47	mm
Emitter pad size	2.995 x 2.901	
Gate pad size	1.107 x 0.702	
Area total / active	19.7 / 12.8	mm <sup>2</sup>
Thickness	140	µm
Wafer size	150	mm
Flat position	0	grd
Max.possible chips per wafer	748 pcs	
Passivation frontside	Photoimide	
Emitter metallization	3200 nm AlSiCu	
Collector metallization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, <500µm	
Reject Ink Dot Size	Ø 0.65mm ; max 1.2mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	



# SIGC20T120

## MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_j=25\text{ }^\circ\text{C}$	$V_{CE}$	1200	V
DC collector current, limited by $T_{j\max}$	$I_C$	<sup>1)</sup>	A
Pulsed collector current, $t_p$ limited by $T_{j\max}$	$I_{cpuls}$	45	A
Gate emitter voltage	$V_{GE}$	$\pm 20$	V
Operating junction and storage temperature	$T_j, T_{stg}$	-55 ... +150	$^\circ\text{C}$

<sup>1)</sup> depending on thermal properties of assembly

**STATIC CHARACTERISTICS (tested on chip)**,  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0\text{V}$ , $I_C=0.5\text{mA}$	1200			
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$V_{GE}=15\text{V}$ , $I_C=15\text{A}$	1.4	1.7	2.1	V
Gate-emitter threshold voltage	$V_{GE(\text{th})}$	$I_C=600\mu\text{A}$ , $V_{GE}=V_{CE}$	5.0	5.8	6.5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200\text{V}$ , $V_{GE}=0\text{V}$			2.16	$\mu\text{A}$
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0\text{V}$ , $V_{GE}=20\text{V}$			120	nA
Integrated gate resistor	$R_{Gint}$			--		$\Omega$

**ELECTRICAL CHARACTERISTICS** (tested at component):

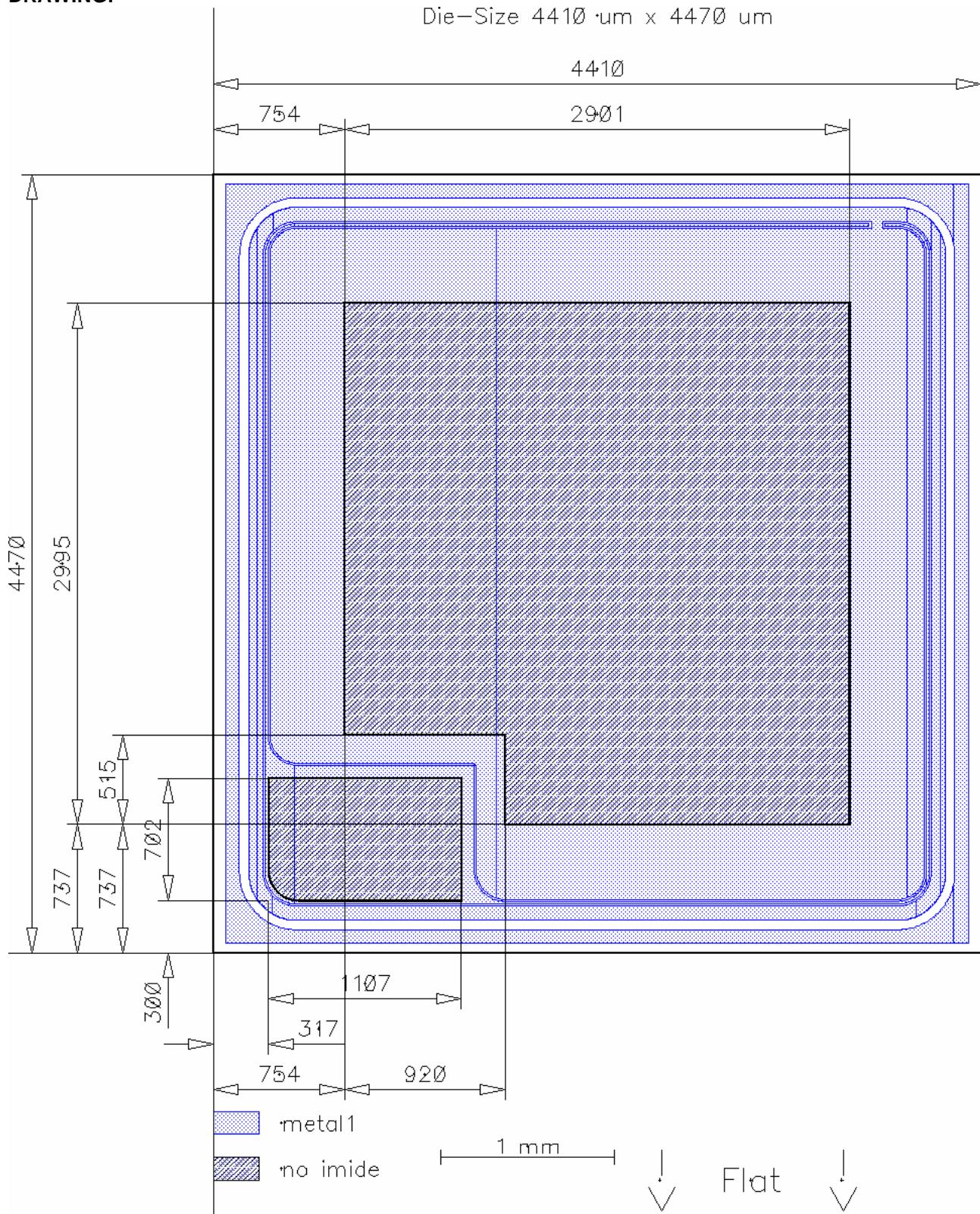
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	$C_{iss}$	$V_{CE}=25\text{V}$ ,		1090		pF
Output capacitance	$C_{oss}$	$V_{GE}=0\text{V}$ ,		58		
Reverse transfer capacitance	$C_{rss}$	$f=1\text{MHz}$		48		

**SWITCHING CHARACTERISTICS** (tested at component), Inductive Load

Parameter	Symbol	Conditions <sup>1)</sup>	Value			Unit
			min.	typ.	max.	
Turn-on delay time	$t_{d(on)}$	$T_j=125\text{ }^\circ\text{C}$		90		ns
Rise time	$t_r$	$V_{CC}=600\text{V}$ , $I_C=15\text{A}$ ,		45		
Turn-off delay time	$t_{d(off)}$	$V_{GE}=-15/15\text{V}$ , $R_G= 75\Omega$		520		
Fall time	$t_f$			90		

<sup>1)</sup> values also influenced by parasitic L- and C- in measurement and package.

## CHIP DRAWING:





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## FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet	tbd	
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## DESCRIPTION:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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